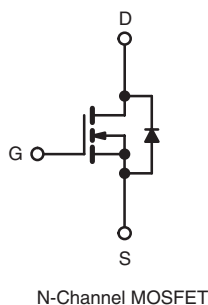
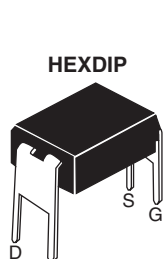


Power MOSFET

PRODUCT SUMMARY

V_{DS} (V)	500	
$R_{DS(on)}$ (Ω)	$V_{GS} = 10\text{ V}$	3.0
Q_g (Max.) (nC)	24	
Q_{gs} (nC)	3.3	
Q_{gd} (nC)	13	
Configuration	Single	



FEATURES

- Dynamic dV/dt Rating
- Repetitive Avalanche Rated
- For Automatic Insertion
- End Stackable
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements
- Lead (Pb)-free Available



RoHS*
COMPLIANT

DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The 4 pin DIP package is a low cost machine-insertable case style which can be stacked in multiple combinations on standard 0.1 inch pin centers. The dual drain serves as a thermal link to the mounting surface for power dissipation levels up to 1 W.

ORDERING INFORMATION

Package	HEXDIP
Lead (Pb)-free	IRFD420PbF SiHFD420-E3
SnPb	IRFD420 SiHFD420

ABSOLUTE MAXIMUM RATINGS $T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V_{DS}	500	V
Gate-Source Voltage			V_{GS}	± 20	
Continuous Drain Current	V_{GS} at 10 V	$T_C = 25\text{ }^{\circ}\text{C}$	I_D	0.37	A
		$T_C = 100\text{ }^{\circ}\text{C}$		0.23	
Pulsed Drain Current ^a			I_{DM}	3.0	
Linear Derating Factor				0.0083	W/ $^{\circ}\text{C}$
Single Pulse Avalanche Energy ^b			E_{AS}	51	mJ
Repetitive Avalanche Current ^a			I_{AR}	0.37	A
Repetitive Avalanche Energy ^a			E_{AR}	0.10	mJ
Maximum Power Dissipation	$T_C = 25\text{ }^{\circ}\text{C}$		P_D	1.0	W
Peak Diode Recovery dV/dt^c			dV/dt	3.5	V/ns
Operating Junction and Storage Temperature Range			T_J, T_{stg}	- 55 to + 150	$^{\circ}\text{C}$
Soldering Recommendations (Peak Temperature)	for 10 s			300 ^d	

Notes

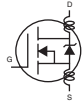
- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 50\text{ V}$, starting $T_J = 25\text{ }^\circ\text{C}$, $L = 40\text{ mH}$, $R_G = 25\text{ }\Omega$, $I_{AS} = 1.5\text{ A}$.
- $I_{SD} \leq 4.4\text{ A}$, $dI/dt \leq 90\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DS}$, $T_J \leq 150\text{ }^\circ\text{C}$.
- 1.6 mm from case.

* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	120	°C/W

SPECIFICATIONS $T_J = 25\text{ °C}$, unless otherwise noted

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		500	-	-	V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	Reference to 25 °C, I _D = 1 mA		-	0.59	-	V/°C
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		2.0	-	4.0	V
Gate-Source Leakage	I _{GSS}	V _{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 500 V, V _{GS} = 0 V		-	-	25	μA
		V _{DS} = 400 V, V _{GS} = 0 V, T _J = 125 °C		-	-	250	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 0.22 A ^b	-	-	3.0	Ω
Forward Transconductance	g _{fs}	V _{DS} = 50 V, I _D = 1.3 A ^b		1.5	-	-	S
Dynamic							
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1.0 MHz		-	360	-	pF
Output Capacitance	C _{oss}			-	92	-	
Reverse Transfer Capacitance	C _{rss}			-	37	-	
Total Gate Charge	Q _g	V _{GS} = 10 V	I _D = 2.1 A, V _{DS} = 400 V ^b	-	-	24	nC
Gate-Source Charge	Q _{gs}			-	-	3.3	
Gate-Drain Charge	Q _{gd}			-	-	13	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 250 V, I _D = 2.1 A, R _G = 18 Ω, R _D = 120 Ω ^b		-	8.0	-	ns
Rise Time	t _r			-	8.6	-	
Turn-Off Delay Time	t _{d(off)}			-	33	-	
Fall Time	t _f			-	16	-	
Internal Drain Inductance	L _D	Between lead, 6 mm (0.25") from package and center of die contact 		-	4.0	-	nH
Internal Source Inductance	L _S			-	6.0	-	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I _S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	0.37	A
Pulsed Diode Forward Current ^a	I _{SM}			-	-	5.0	
Body Diode Voltage	V _{SD}	T _J = 25 °C, I _S = 0.37 A, V _{GS} = 0 V ^b		-	-	1.6	V
Body Diode Reverse Recovery Time	t _{rr}	T _J = 25 °C, I _F = 2.1 A, dI/dt = 100 A/μs ^b		-	260	520	ns
Body Diode Reverse Recovery Charge	Q _{rr}			-	0.70	1.4	μC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L _S and L _D)					

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

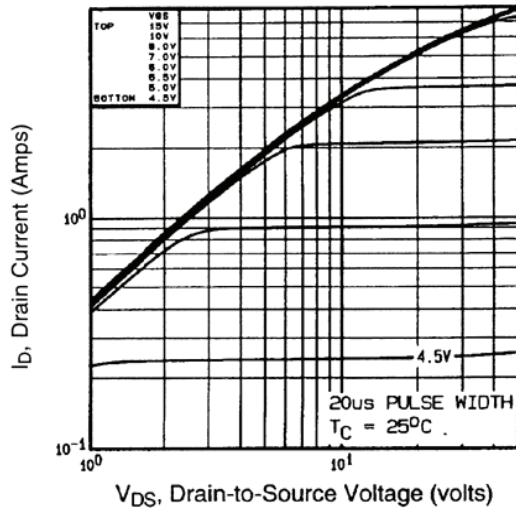


Fig. 1 - Typical Output Characteristics, $T_C = 25^\circ\text{C}$

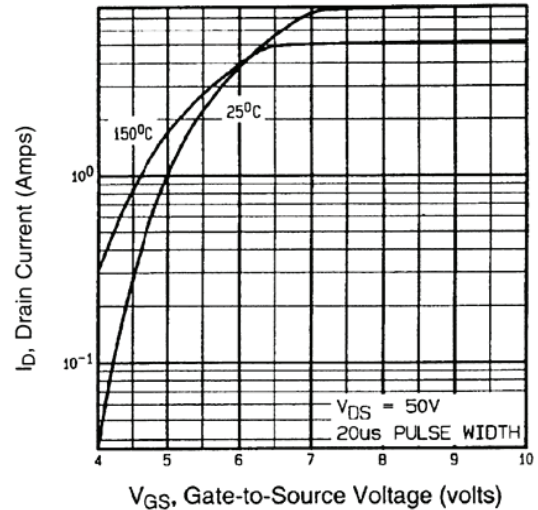


Fig. 3 - Typical Transfer Characteristics

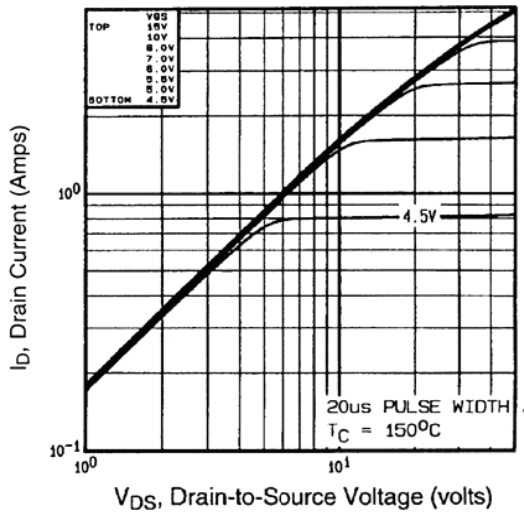


Fig. 2 - Typical Output Characteristics, $T_C = 150^\circ\text{C}$

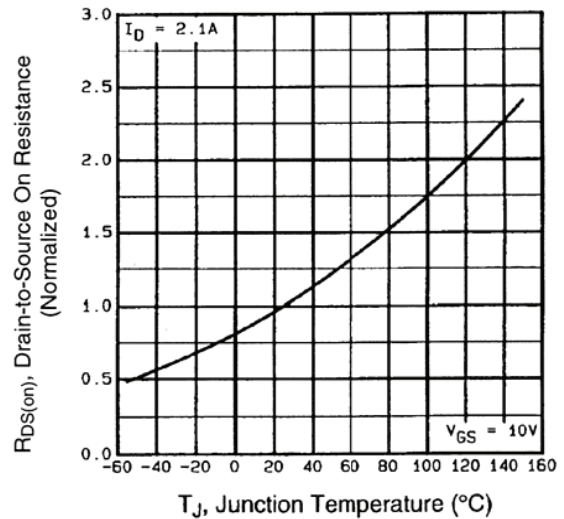


Fig. 4 - Normalized On-Resistance vs. Temperature

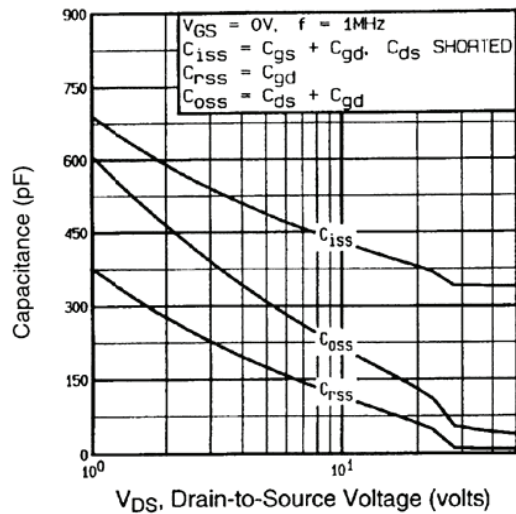


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

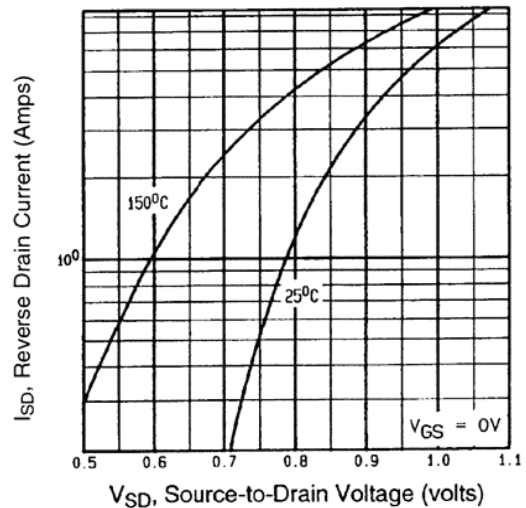


Fig. 7 - Typical Source-Drain Diode Forward Voltage

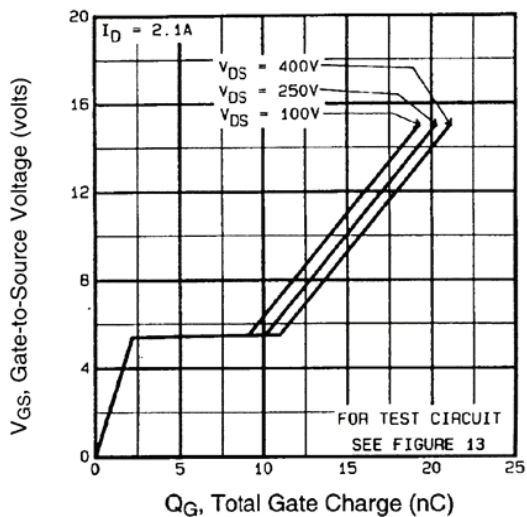


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

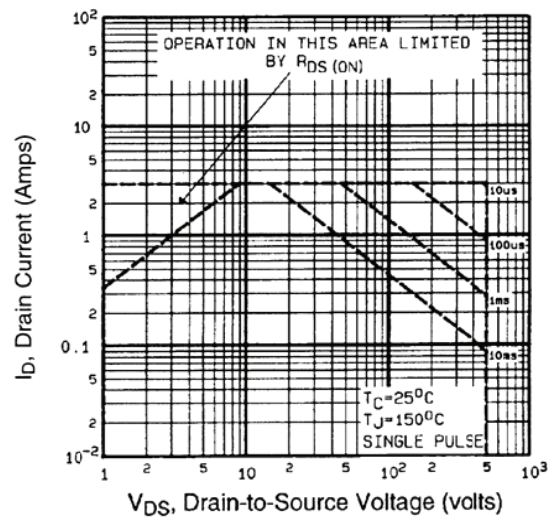


Fig. 8 - Maximum Safe Operating Area

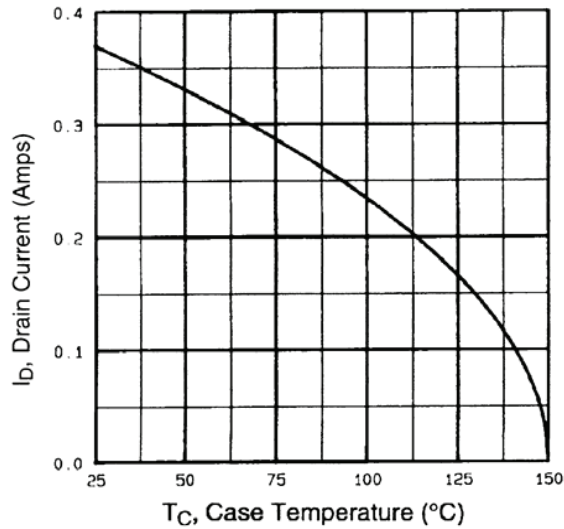


Fig. 9 - Maximum Drain Current vs. Case Temperature

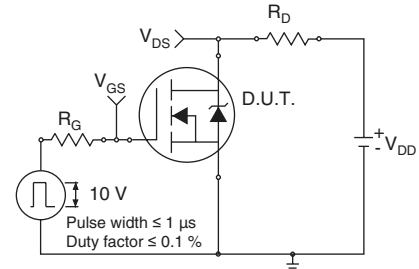


Fig. 10a - Switching Time Test Circuit

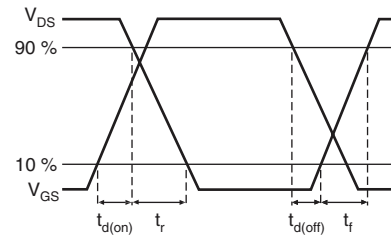


Fig. 10b - Switching Time Waveforms

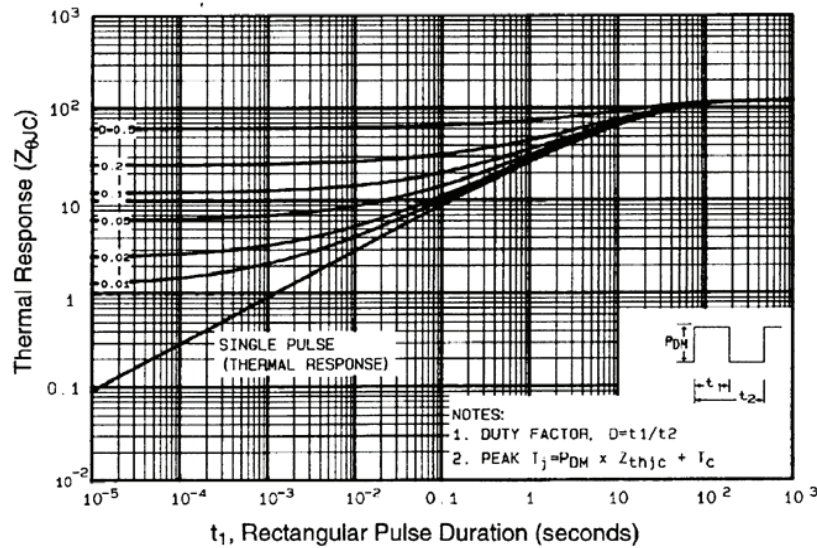


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

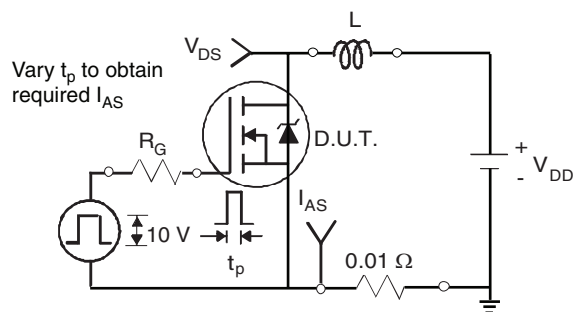


Fig. 12a - Unclamped Inductive Test Circuit

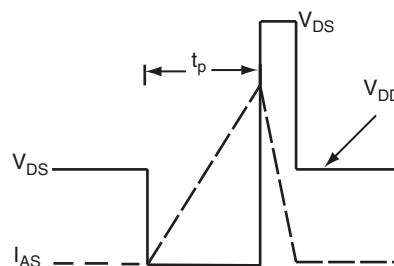


Fig. 12b - Unclamped Inductive Waveforms

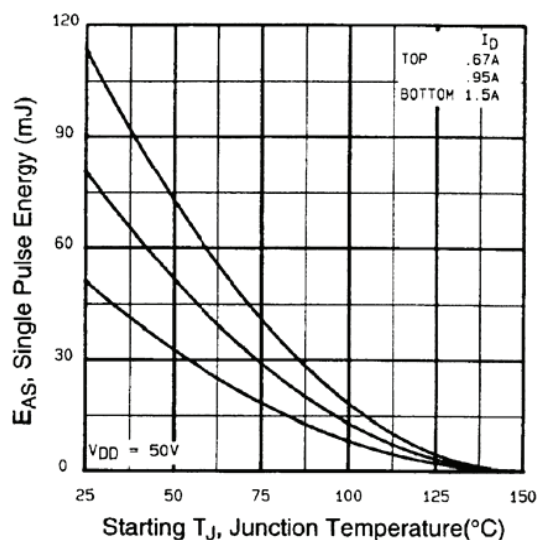


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

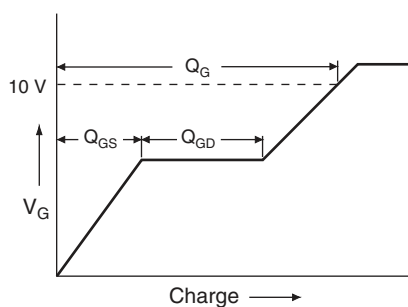


Fig. 13a - Basic Gate Charge Waveform

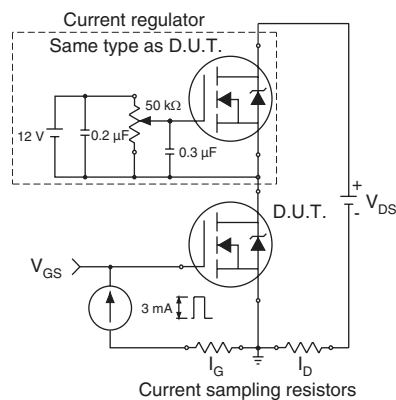


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit

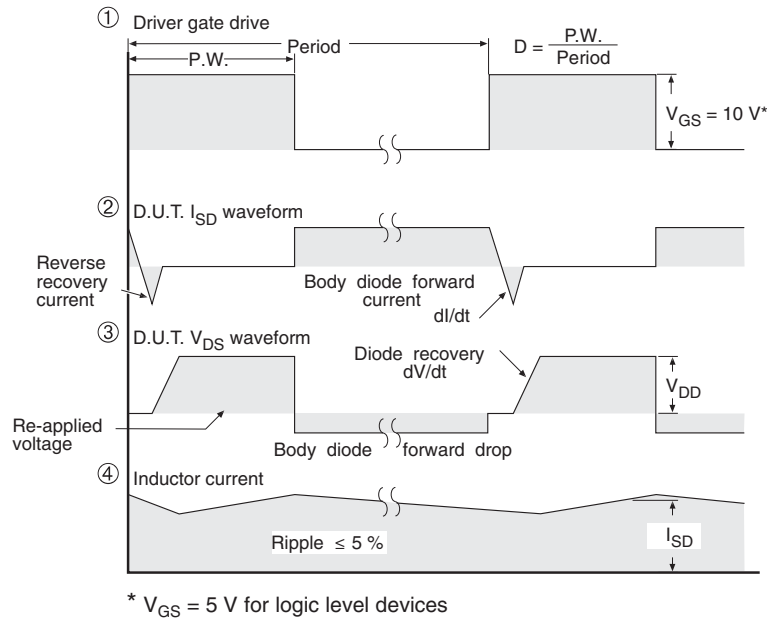
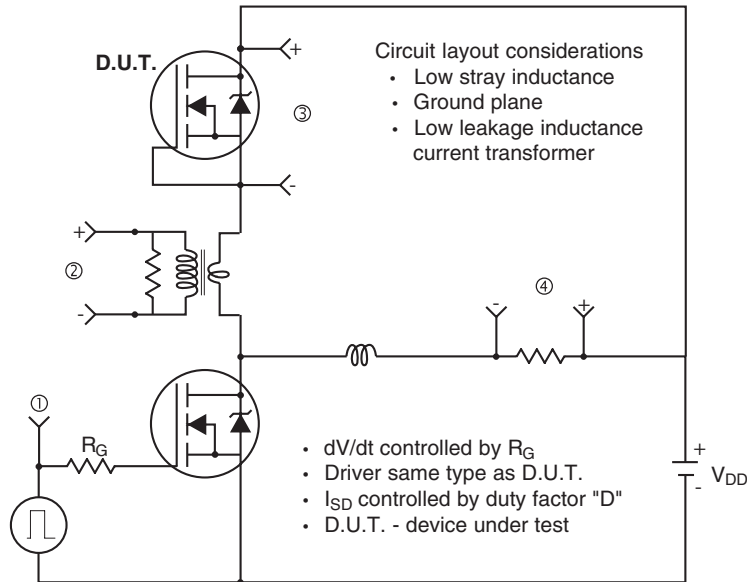


Fig. 14 - For N-Channel

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